

**UNIVERSITI TEKNOLOGI MARA  
CAWANGAN PULAU PINANG**

**STUDY OF REDUCED SELF-  
HEATING EFFECT IN  $\beta$  Ga<sub>2</sub>O<sub>3</sub>  
ON A DIFFERENT SUBSTRATES  
UTILIZING SILVACO TCAD**

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## AUTHOR'S DECLARATION

I declare that the work in this thesis was carried out in accordance with the regulations of Universiti Teknologi MARA. It is original and is the results of my own work, unless otherwise indicated or acknowledged as referenced work.

I, hereby, acknowledge that I have been supplied with the Academic Rules and Regulations, Universiti Teknologi MARA, regulating the conduct of my study and research.

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## ABSTRACT

The architecture of high-power electronics proficient of operating at high temperatures without the need for comprehensive device heat reduction is desirable in wide sectors mainly industrial  $\beta\text{-Ga}_2\text{O}_3$  is a preferable wide band gap semiconductor for having good electrical properties suitable for power applications. However  $\beta\text{-Ga}_2\text{O}_3$  suffers low thermal conductivity ( $\sim 0.2\text{Wcm}^{-1}\text{K}^{-1}$ ). The problem resulting in poor heat dissipation, it called self-heating effect which reduce carrier mobility and drain current degradation. Thus, the project was conducted using simulation software from SILVACO TCAD to investigate  $\beta\text{-Ga}_2\text{O}_3$  fabricated on different substrates which is 4H-SiC, Silicon and  $\beta\text{-Ga}_2\text{O}_3$ . The structures created is to mitigate the problem to helps improve device performances. This research aim is to study the effect of reduced self-heating effect in  $\beta\text{-Ga}_2\text{O}_3$  MOSFET on different substrates utilizing SILVACO TCAD. I-V characteristic was analysed to evaluate and determine the performance of the device on various substrates helps to reduce the self-heating effect on the device. The results of the study shows that the drain current increases and slowly degrades specifically for Silicon substrates. The simulation found that 4H-SiC as hetero-epitaxial substrates helps to reduce the problem faced on  $\beta\text{-Ga}_2\text{O}_3$  device by increasing origin drain current by 32.67% from 50.81mA to 67.41mA at  $V_g=8\text{V}$ . Hence, 4H-SiC is suitable substrate to increase the performance and reduce the self-heating effect of  $\beta\text{-Ga}_2\text{O}_3$  substrates.

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# TABLE OF CONTENTS

	<b>PAGE</b>
<b>AUTHOR'S DECLARATION</b>	<b>i</b>
<b>ABSTRACT</b>	<b>ii</b>
<b>ACKNOWLEDGEMENT</b>	<b>iii</b>
<b>TABLE OF CONTENTS</b>	<b>iv</b>
<b>LIST OF TABLES</b>	<b>vii</b>
<b>LIST OF FIGURES</b>	<b>viii</b>
<b>LIST OF APPENDICES</b>	<b>ix</b>
<b>LIST OF SYMBOLS</b>	<b>x</b>
<b>LIST OF ABBREVIATIONS</b>	<b>xi</b>
<b>CHAPTER 1 INTRODUCTION</b>	<b>1</b>
1.1 Research Background	1
1.2 Problem Statement	3
1.3 Objectives	4
1.4 Scope of Work	4
1.5 Significance of Study	4
1.6 Thesis Organization	5
<b>CHAPTER 2 LITERATURE REVIEW</b>	<b>7</b>
2.1 Introduction	7
2.2 Related Previous Research	7
2.2.1 Overview of High Power Application	7
2.2.2 Problem Found in Silicon High Power MOSFET	8
2.2.3 Choices of Wide bandgap Material for High Power MOSFET	10
2.3 Research of Material Purposed	12
2.3.1 Foundational Technology in Semiconductor (Silicon)	12
2.3.2 Beta-Gallium Oxide ( $\beta$ -Ga <sub>2</sub> O <sub>3</sub> )	14
2.3.3 Silicon Carbide (4H-SiC)	17

2.4	This Work	20
2.5	Summary	20
<b>CHAPTER 3 RESEARCH METHODOLOGY</b>		<b>21</b>
3.1	Introduction	21
3.2	Device Simulator Atlas	21
3.3	Development of $\beta$ - $\beta$ - $Ga_2O_3$ MOSFET Device With Different Substrates	24
3.4	Simulation Parameters	26
3.5	Process To Simulate The Design	27
3.5.1	Define Mesh Statement	28
3.5.2	Define Region Statement	28
3.5.3	Define Electrode Statement	29
3.5.4	Define Doping Statement	29
3.5.5	Define Material and Model Statement	30
3.5.6	Define Numerical Method Statement	31
3.5.7	Obtain Solution	32
3.6	Summary	32
<b>CHAPTER 4 RESULTS AND DISCUSSION</b>		<b>33</b>
4.1	Introduction	33
4.2	Final Structure of MOSFET	33
4.3	I-V characteristic	36
4.3.1	ID vs VD (Drain current vs Drain voltage)	36
4.4.1	ID vs VD for $\beta$ - $Ga_2O_3$ on $\beta$ - $Ga_2O_3$ structure	37
4.4.2	ID vs VD for $\beta$ - $Ga_2O_3$ on various material structure	38
4.5	Summary	41
<b>CHAPTER 5 CONCLUSION AND FUTURE WORK</b>		<b>42</b>
5.1	Introduction	42
5.2	Conclusion	42
5.3	Future Work	43